

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SB595

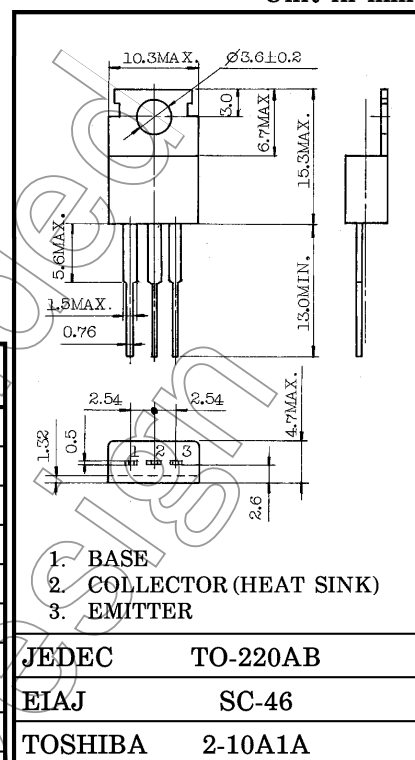
POWER AMPLIFIER APPLICATIONS.

- High Breakdown Voltage : $V_{CEO} = -100V$
- Low Collector-Emitter Saturation Voltage : $V_{CE(sat)} = -2.0V$ (Max.)
- Complementary to 2SD525.
- Recommended for 30W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-5	A
Emitter Current	I_E	-5	A
Base Current	I_B	-4	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	40	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Unit in mm

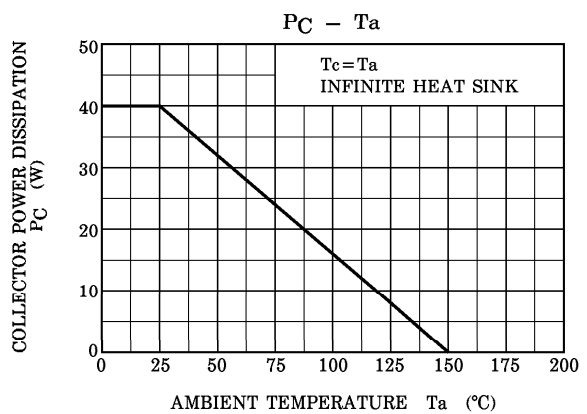
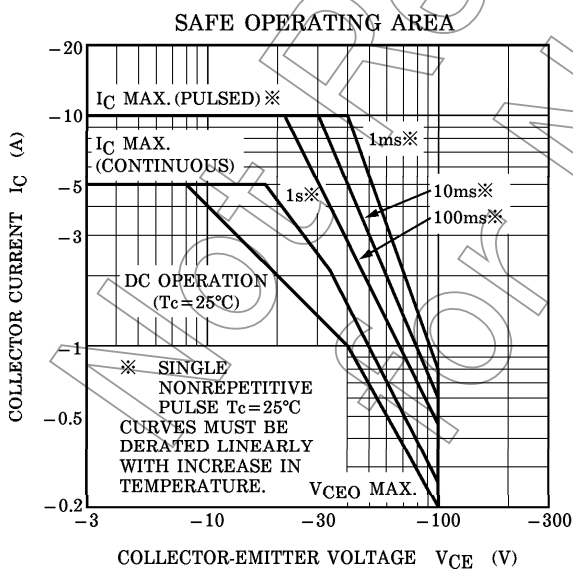
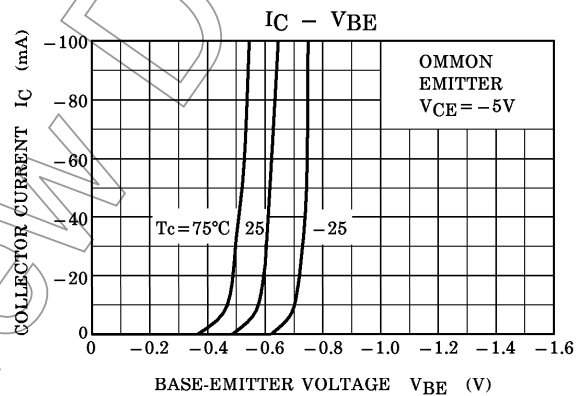
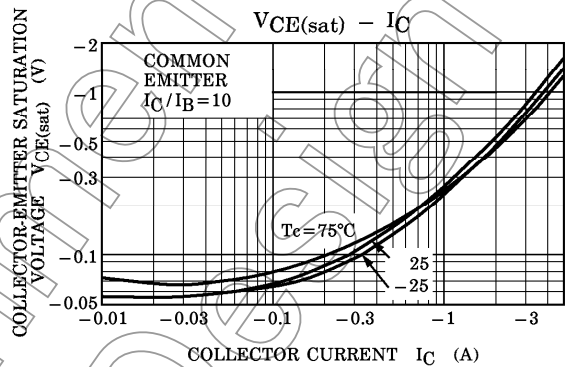
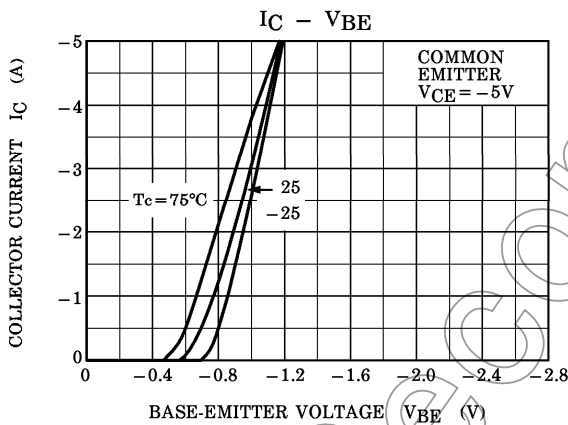
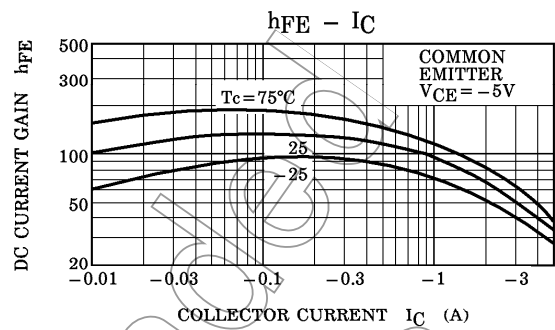
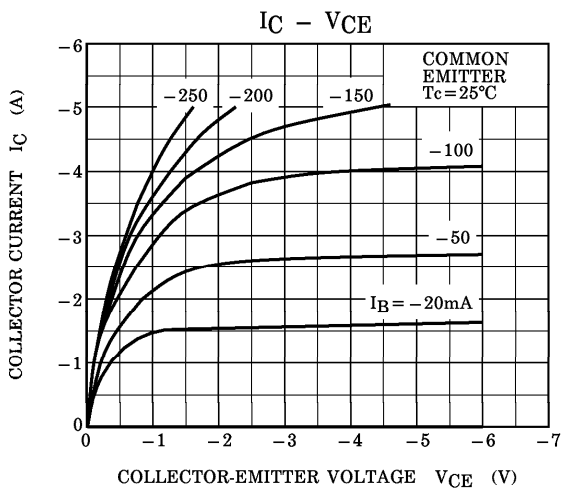


Mounting kit No.AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -100V, I_E = 0$	—	—	-100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-100	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C = -10mA, I_C = 0$	-5	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -5V, I_C = -1A$	40	—	240	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -4A$	20	—	—	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4A, I_C = -0.4A$	—	—	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -4A$	—	—	-1.5	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -1A$	—	5	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	270	—	pF

Note : $h_{FE(1)}$ Classification R : 40~80, O : 70~140, Y : 120~240



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